

Schottky Dual Diode

MBR2550CT

50V / 30A

DATASHEET

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OEM – General Semiconductor

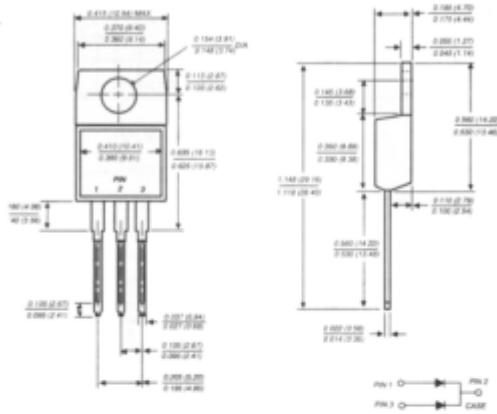
Source: General Semiconductor Databook 1998

MBR2535CT THRU MBR2560CT

SCHOTTKY RECTIFIER

Reverse Voltage - 35 to 60 Volts Forward Current - 30.0 Amperes

TO-220AB



FEATURES

- Plastic package has Underwriters Laboratory Flammability Classifications 94V-0
- Dual rectifier construction, positive center-tap
- Metal silicon junction, majority carrier conduction
- Low power loss, high efficiency
- High current capability, low forward voltage drop
- High surge capability
- For use in low voltage, high frequency inverters, free wheeling, and polarity protection applications
- Guardring for overvoltage protection
- High temperature soldering guaranteed: 250°C/10 seconds, 0.25" (6.35mm) from case



MECHANICAL DATA

Case: JEDEC TO-220AB molded plastic body
Terminals: Lead solderable per MIL-STD-750, Method 2026
Polarity: As marked
Mounting Position: Any **Mounting Torque:** 5 in. - lbs. max.
Weight: 0.08 ounce, 2.24 grams

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Ratings at 25°C ambient temperature unless otherwise specified.

	SYMBOLS	MBR2535CT	MBR2545CT	MBR2550CT	MBR2560CT	UNITS
Maximum repetitive peak reverse voltage	VRRM	35	45	50	60	Volts
Maximum working peak reverse voltage	VRWM	35	45	50	60	Volts
Maximum DC blocking voltage	VDC	35	45	50	60	Volts
Maximum average forward rectified current at T _C =130°C	I(AV)	30.0				Amps
Peak repetitive forward current per leg at T _C =130°C (rated V _R , square wave, 20 KHz)	IFRM	30.0				Amps
Peak forward surge current 8.3ms single half sine-wave superimposed on rated load (JEDEC Method)	IFSM	150.0				Amps
Peak repetitive reverse surge current (NOTE 1)	IRRM	1.0		0.5		Amps
Maximum instantaneous forward voltage I _F =15.0A, T _C =25°C per leg at: (NOTE 2)	V _F	-		0.75		Volts
I _F =15.0A, T _C =25°C		-		0.65		
I _F = 30A, T _C =25°C		0.82		-		
I _F = 30A, T _C =125°C		0.73		-		
Maximum instantaneous reverse current at rated DC blocking voltage per leg (NOTE 2)	I _R	0.2		1.0		mA
T _C =125°C		40.0		50.0		
Maximum thermal resistance (NOTE 3)	R _{θJC}	1.5				°C/W
Voltage rate of change (rated V _R)	dv/dt	10,000				V/μs
Operating junction temperature range	T _J	-65 to +150				°C
Storage temperature range	T _{STG}	-65 to +175				°C

NOTES:

- (1) 2.0μs pulse width, f=1.0 KHz
- (2) Pulse test: 300μs pulse width, 1% duty cycle
- (3) Thermal resistance from junction to case per leg

RATINGS AND CHARACTERISTIC CURVES MBR2535CT THRU MBR2560CT

